

EAST (10073116.wsp.1)

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L1: (16) (MRAM (magnetic near4 memory)) and ((magnet\$2 near3 tunnel\$3 near3 junction))

L2: (47) (MRAM (magnetic near4 memory)) and ((MTJ (magnet\$2 near3 tunnel\$3 near3 junction))

L3: (4736) MTJ (magnet\$2 near3 tunnel\$3 near3 junction) TMR (tunnel\$3 near3 junction)

L4: (62) (MRAM (magnetic near4 memory)) and (L3 with source) and (L3 with gate)

(40517) MRAM (magnetic near4 memory)

(3376) (MRAM (magnetic near4 memory)) and ((magnet\$2 ferromagnet\$2) adj2 layer)

(996) magnet\$2 near3 tunnel\$3 near3 junction

(517) ((MRAM (magnetic near4 memory)) and ((magnet\$2 ferromagnet\$2) adj2 layer))

(10) ((MRAM (magnetic near4 memory)) and ((magnet\$2 ferromagnet\$2) adj2 layer))

(0) (MRAM (magnetic near4 memory)) and ((magnet\$2 adj2 tunnel\$3) near3 source) and

(1) (MRAM (magnetic near4 memory)) and ((magnet\$2 near3 tunnel\$3 near3 junction))

(0) (MRAM (magnetic near4 memory)) and ((junction adj3 end) near3 gate) and ((junction

(4411) mizushima.in.

(173) (mizushima near koichi).in.

(26) ((mizushima near koichi).in.) and magnetic

(26) ((mizushima near koichi).in.) and magnet\$3

Browser Queue View

DB: LUSPAT: US POFUB: EPO: JPO: DERWENT: IGM: 100

Default operator: OR

Highlight all hit terms only

(MRAM (magnetic near4 memory)) and (L3 with source) and (L3 with gate)

| | U | I | Document ID | Issue Date | Pages | Title | Current OR | Current XRef | Retrieval C | Inventor | S | C | P | T | U | A |
|---|--------------------------|--------------------------|----------------------|------------|-------|---|------------|---------------------|-------------|------------------------|-------------------------------------|--------------------------|--------------------------|--------------------------|--------------------------|--------------------------|
| 1 | <input type="checkbox"/> | <input type="checkbox"/> | US 20040008556 A1 | 20040115 | 33 | Memory device reading data according to difference in | 365/210 | 365/158; 365/173 | | Hidaka, Hideto | <input checked="" type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> |
| 2 | <input type="checkbox"/> | <input type="checkbox"/> | US 20030227799 A1 | 20031211 | 13 | Tunnel magnetoresistive effect element, method of | 365/200 | | | Higo, Yutaka et al. | <input checked="" type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> |
| 3 | <input type="checkbox"/> | <input type="checkbox"/> | US 20030223203 A1 | 20031204 | 71 | Magnetic memory device | 365/200 | | | Kunikiyo, Tatsuya | <input checked="" type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> |
| 4 | <input type="checkbox"/> | <input type="checkbox"/> | US 20030218901 A1 | 20031127 | 41 | Thin film magnetic memory device having an access | 365/157 | | | Ooishi, Tsukasa et al. | <input checked="" type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> |
| 5 | <input type="checkbox"/> | <input type="checkbox"/> | US 20030214039 A1 | 20031120 | 7 | Magnetic random access memory | 365/173 | | | Jang, In Woo et al. | <input checked="" type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> |
| 6 | <input type="checkbox"/> | <input type="checkbox"/> | US 20030202407 A1 | 20031030 | 40 | MEMORY DEVICE HAVING WIDE MARGIN OF DATA READING | 365/200 | | | Hidaka, Hideto | <input checked="" type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> |
| 7 | <input type="checkbox"/> | <input type="checkbox"/> | US 20030196080 A1 | 20031023 | 209 | Magnetic random access memory | 365/150 | | | Iwata, Yoshihisa | <input checked="" type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> |

Ready

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